

NextPower 100 V, 7 m $\Omega$  N-channel MOSFET in LFPAK56 package

8 December 2017

Product data sheet

### 1. General description

NextPower 100 V standard level gate drive MOSFET. Qualified to 175 °C and recommended for industrial & consumer applications.

### 2. Features and benefits

- Low Q<sub>rr</sub> for higher efficiency and lower spiking
- Qualified to 175 °C
- Low Q<sub>G</sub> x R<sub>DSon</sub> FOM for high efficiency switching applications
- Strong avalanche energy rating (E<sub>as</sub>)
- Avalanche rated and 100% tested
- Ha-free and RoHS compliant LFPAK56 package
- Wave-solderable LFPAK56 package

### 3. Applications

- Synchronous rectifier in AC-DC and DC-DC
- BLDC motor control
- USB-PD and mobile fast-charge adapters
- LED lighting
- Full-bridge and half-bridge applications
- Flyback and resonant topologies

### 4. Quick reference data

Table 1. Quick	reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	100	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	-	90	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	-	238	W
Static character	eristics					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 10	-	5.6	7	mΩ
Dynamic char	acteristics					
Q <sub>GD</sub>	gate-drain charge	$I_D$ = 25 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V; Fig. 12; Fig. 13	-	10.3	-	nC
Source-drain	diode					
Q <sub>r</sub>	recovered charge	$I_{S}$ = 25 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; <u>Fig. 16</u>	-	52.4	-	nC

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### 5. Pinning information

Table 2. Pinning information								
Pin	Symbol	Description	Simplified outline	Graphic symbol				
1	S	source	mb	D				
2	S	source	ل <del>ا دے ا</del>					
3	S	source	q	G				
4	G	gate		mbb076 S				
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)					

### 6. Ordering information

Table 3. Ordering information						
Type number	Package	9				
	Name	Description	Version			
PSMN6R9-100YSF	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN6R9-100YSF	6F9S10

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

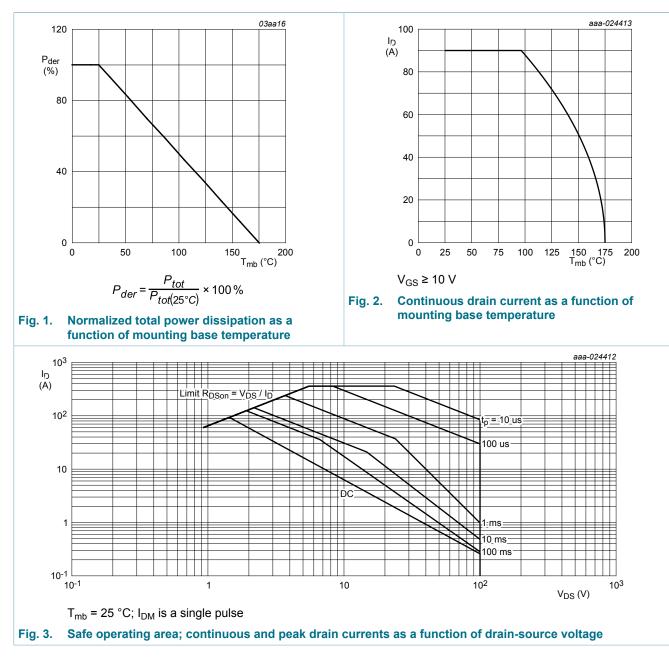
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	100	V
V <sub>DGR</sub>	drain-gate voltage	$25 \text{ °C} \le \text{T}_{j} \le 175 \text{ °C}; \text{R}_{\text{GS}} = 20 \text{ k}\Omega$	-	100	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	238	W
ID	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	90	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	-	88	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3	-	360	А
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
Source-drai	n diode			·		
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	90	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	360	А
Avalanche r	ruggedness			Ì		
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$ \begin{array}{l} {\sf I}_{\sf D} = 36 \; {\sf A};  {\sf V}_{sup} \leq \; 100 \; {\sf V}; \; {\sf R}_{\rm GS} = 50 \; \Omega; \\ {\sf V}_{\rm GS} = 10 \; {\sf V}; \; {\sf T}_{\rm j(init)} = 25 \; {\rm ^{\circ}C}; \; \underline{{\sf Fig. 4}}; \\ {\sf Unclamped} \end{array} $	[1]	-	321	mJ
I <sub>AS</sub>	non-repetitive avalanche current		[1]	-	36	A

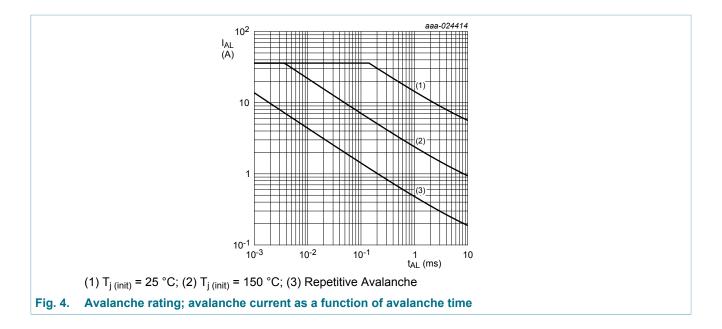
#### [1] Protected by 100% test



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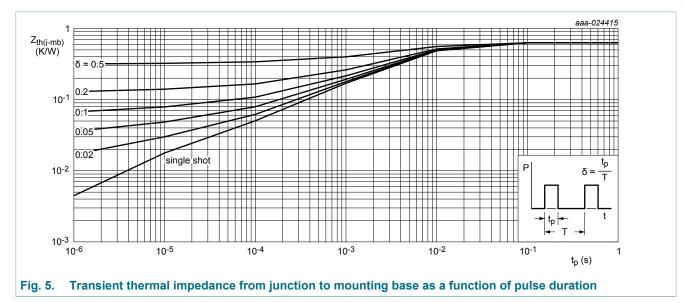
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### 9. Thermal characteristics

#### Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.56	0.63	K/W



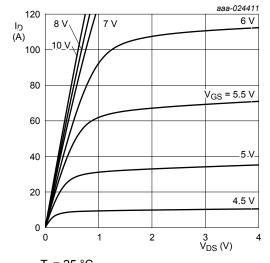
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics		1	-	,	
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	100	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	90	-	-	V
V <sub>GS(th)</sub>	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	3.7	-	V
	voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 175 °C	-	2	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 9$	2	3.3	4	V
$\Delta V_{GS(th)} / \Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-8.4	-	mV/K
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.02	5	μA
		$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 125 °C	-	-	100	μA
GSS	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	5	100	nA
		$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	5	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	5.6	7	mΩ
		$V_{GS}$ = 7 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	6.6	10.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; <u>Fig. 11</u>	-	8.9	10.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; <u>Fig. 11</u>	-	12.5	15.4	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.9	-	Ω
Dynamic cha	racteristics		·			
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 25 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V; Fig. 12; Fig. 13	-	50.3	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	20.9	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$	-	17.1	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	9.9	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	7.2	-	nC
Q <sub>GD</sub>	gate-drain charge		-	10.3	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; <u>Fig. 12; Fig. 13</u>	-	5.1	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 50 V; V_{GS} = 0 V; f = 1 MHz;$	-	3570	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	722	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	19	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	14.8	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C	-	14.2	-	ns

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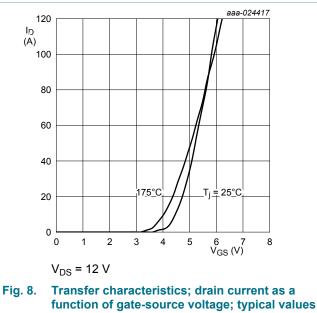
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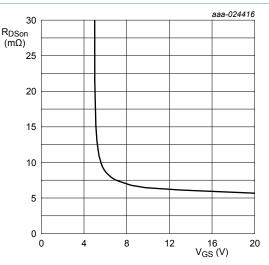
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
t <sub>d(off)</sub>	turn-off delay time			-	27.6	-	ns	
t <sub>f</sub>	fall time			-	16	-	ns	
Source-drain o	Source-drain diode							
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 15</u>		-	0.8	1.2	V	
t <sub>rr</sub>	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 50 \text{ V}; \frac{\text{Fig. 16}}{16}$		-	45.4	-	ns	
Qr	recovered charge			-	52.4	-	nC	

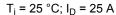




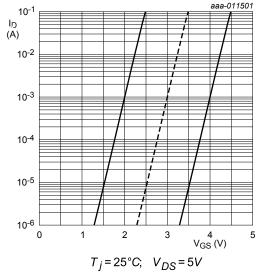








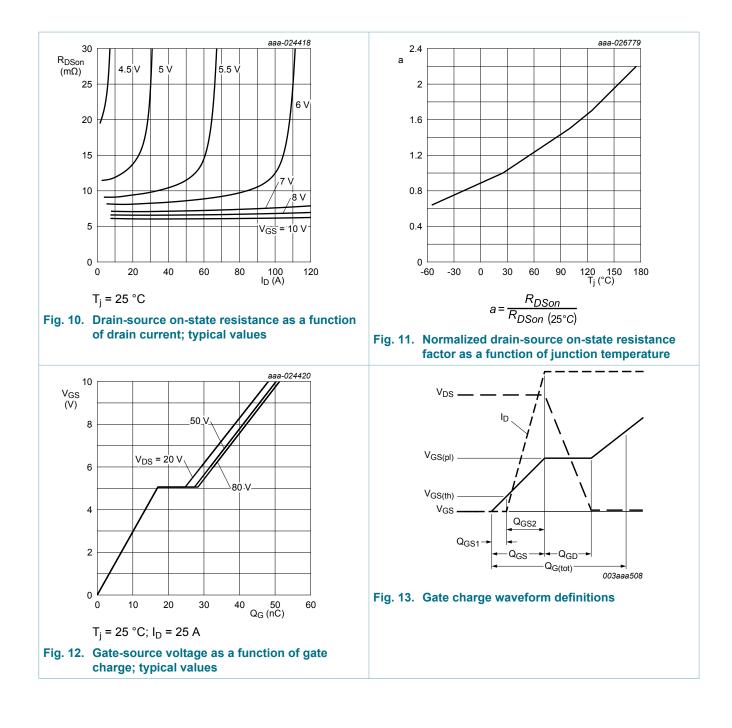




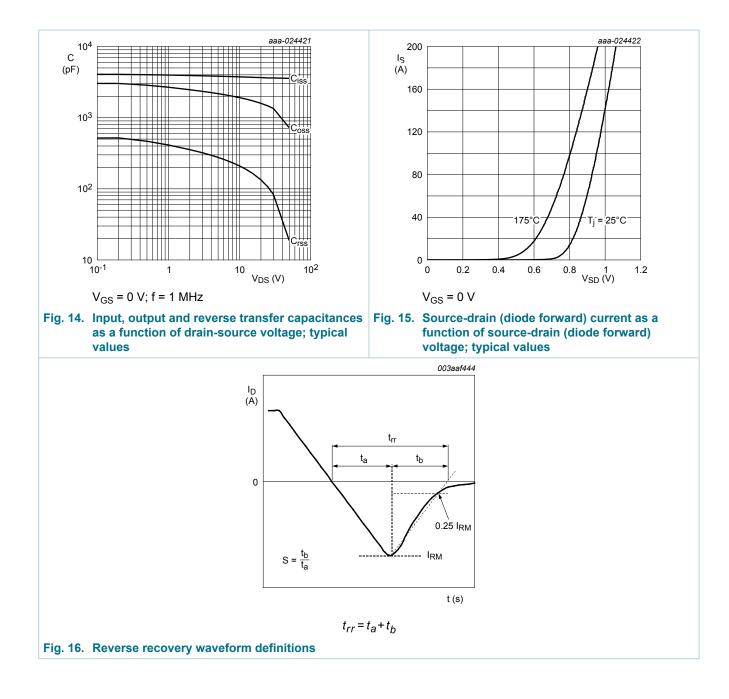


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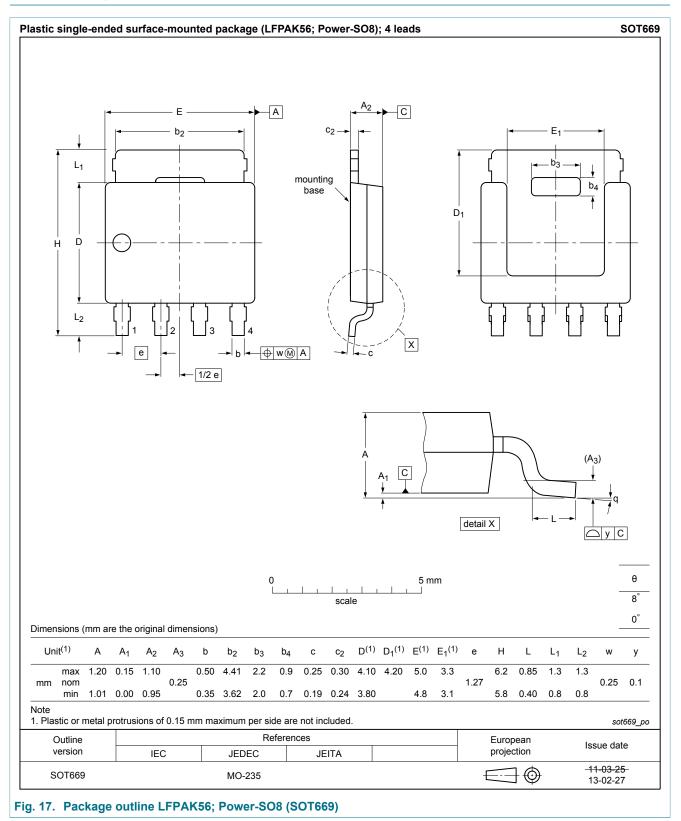
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#### NextPower 100 V, 7 mΩ N-channel MOSFET in LFPAK56 package



### 11. Package outline



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### 12. Soldering

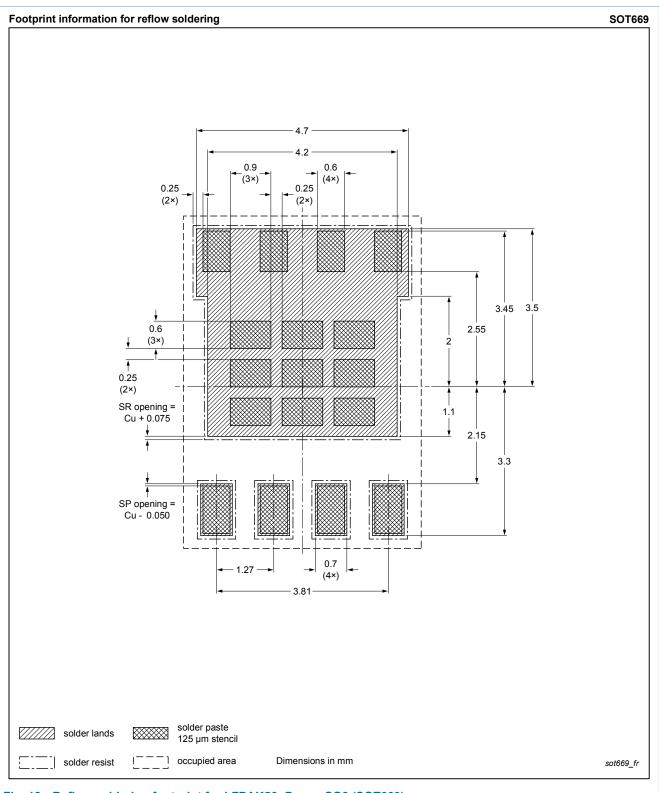
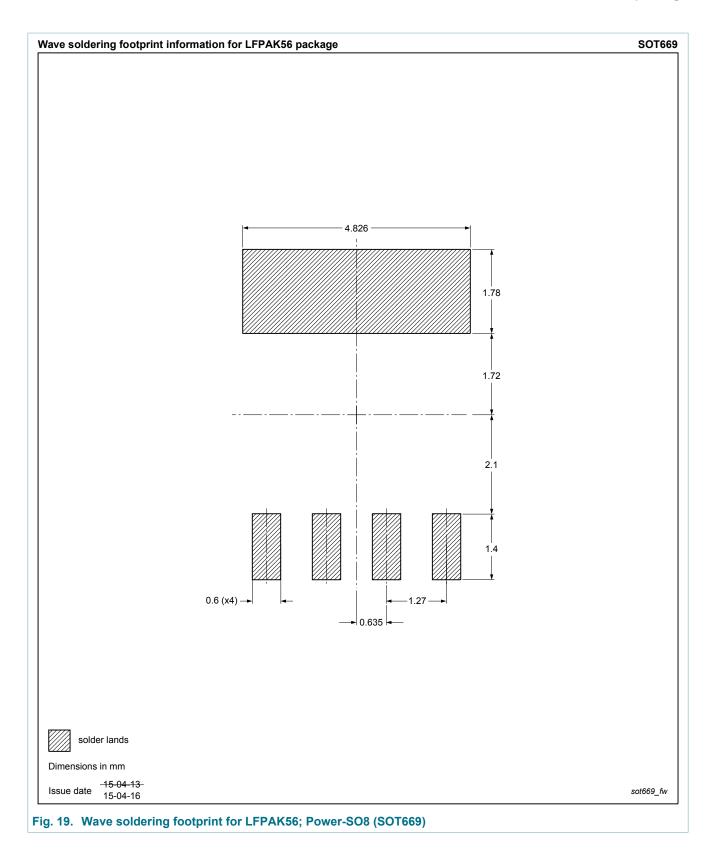


Fig. 18. Reflow soldering footprint for LFPAK56; Power-SO8 (SOT669)

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